Silicon NPN Power Transistors 2SD2300

DESCRIPTION

·With TO-3PFM package
·High breakdown voltage
·Built-in damper diode

APPLICATIONS

·For color TV horizontal output deflection applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

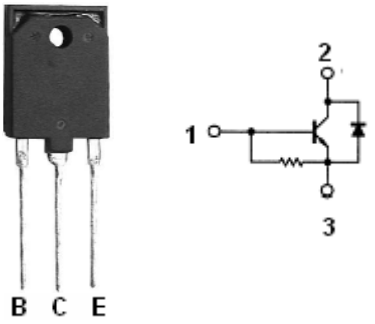

Fig.1 simplified outline (TO-3PFM) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
I_{CM}	Collector current-peak		6	A
$I_{C(surge)}$	Collector surge current		16	A
P_C	Collector power dissipation	T_C=25□	50	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=350mA , I_C=0	6			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=4.5A ; I_B=1.2A			5.0	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=4.5A ; I_B=1.2A			1.5	V
I_{CES}	Collector cut-off current	V_{CE}=1500V; R_{BE}=0			500	μA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V			20	
t_f	Fall time	I_C=4A ; I_{B1}=0.8A; I_{B2}≈-1.5A			1.0	μs
V_F	Diode forward voltage	I_F=6A			3.0	V

PACKAGE OUTLINE

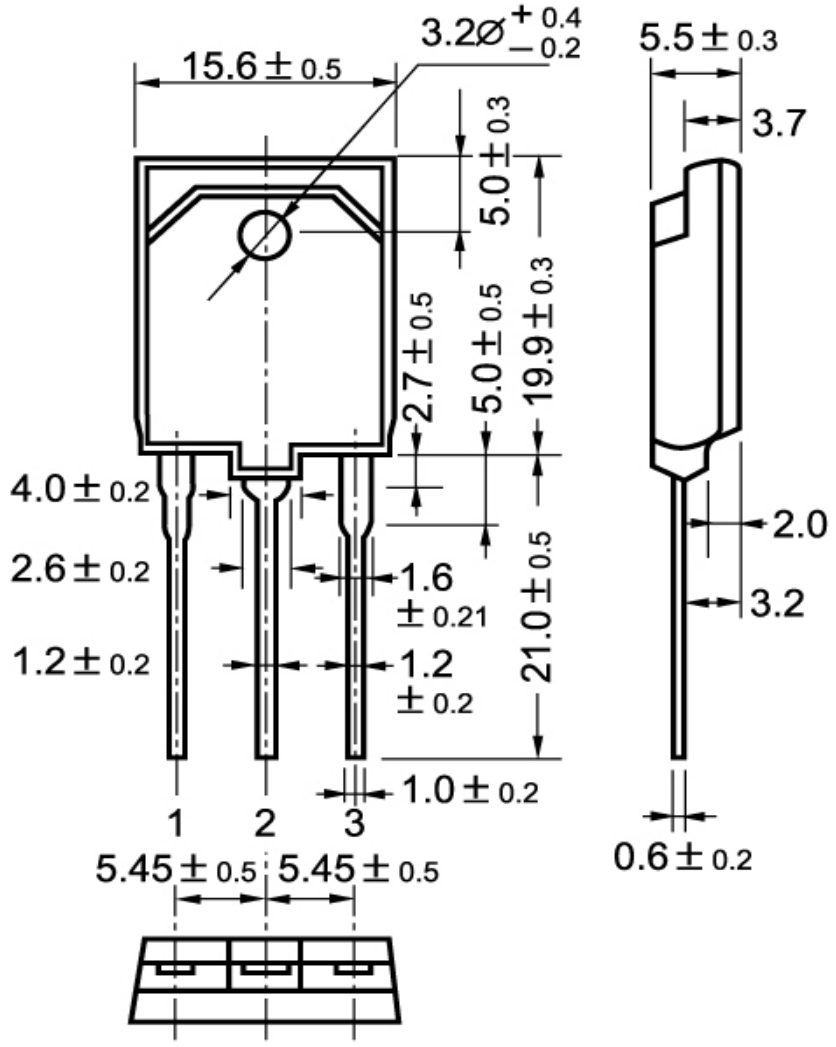

Fig.2 outline dimensions